

We Chim:
Patent Claims
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1. Process for the metallization of at least one insulating layer of an electronic or microelectronic component, whose layer thickness is at most 50 Fm, wherein firstly
- at least one insulating layer is applied to the substrate and is activated by treatment with an activator,
 - then another insulating layer is applied and patterned, and lastly
 - the first insulating layer is seeded and metallized.
2. Process according to Claim 1, in which the two insulating layers are of the same material.
3. Process according to Claim 1 or 2, in which the first insulating layer is patterned before the second insulating layer is applied.

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